

P-Ch -20V Fast Switching MOSFET
 $V_{DS}=-20V$, $I_D=-4.9A$, $R_{DS(ON)}=43m\Omega$

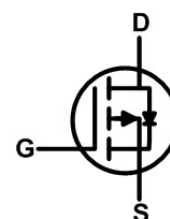
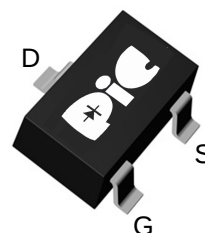
➤ General Description

This PAP2015N P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

➤ SOT-23



➤ Application

- Portable Equipment
- Battery Powered System
- Net Working System

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate –Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^{\circ}C$)	I_D	$T_A=25^{\circ}C$ -4.9	A
		$T_A=70^{\circ}C$ -3.9	
Pulsed Drain Current	I_{DM}	-10	A
Continuous Source Current(Diode Conduction)	I_S	-1.6	A
Power Dissipation	P_D	$T_A=25^{\circ}C$ 1.25	W
		$T_A=70^{\circ}C$ 0.8	
Operating Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{STG}	-55/150	$^{\circ}C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^{\circ}C/W$

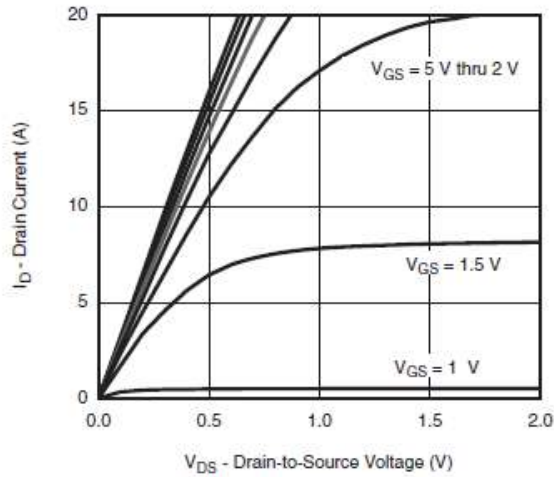
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➤ **Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)**

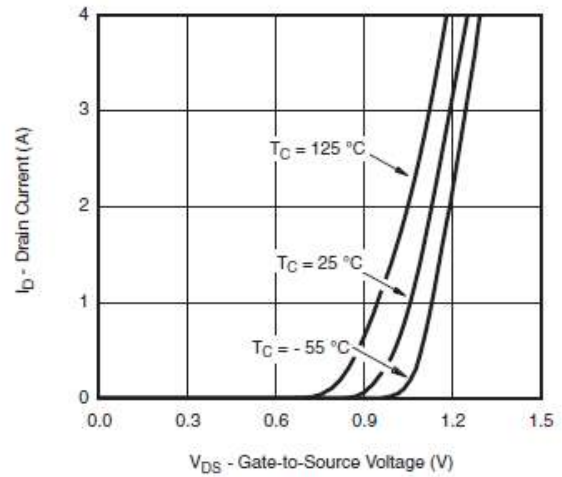
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.73	-1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V$ $T_J=85^\circ C$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq -5V, V_{GS}=-4.5V$	-6			A
		$V_{DS} \geq -5V, V_{GS}=-2.5V$	-4			
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-4.9A$		31	43	mΩ
		$V_{GS}=-2.5V, I_D=-3.4A$		41	55	
		$V_{GS}=-1.8V, I_D=-2.2A$		59	75	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-3.6A$		10		S
Diode Forward Voltage	V_{SD}	$I_S=-1.6A, V_{GS}=0V$		-0.85	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-2.5V$ $I_D=-4.0A$		10	18	nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			3.5		
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V$ $f=1MHz$		1050		pF
Output Capacitance	C_{oss}			165		
Reverse Transfer Capacitance	C_{rss}			135		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.7\Omega$ $I_D=-3.7A, V_{GEN}=-4.5V$ $R_G=1\Omega$		15	25	ns
	t_r			25	40	
Turn-Off Time	$t_{d(off)}$			40	65	
	t_f			15	25	

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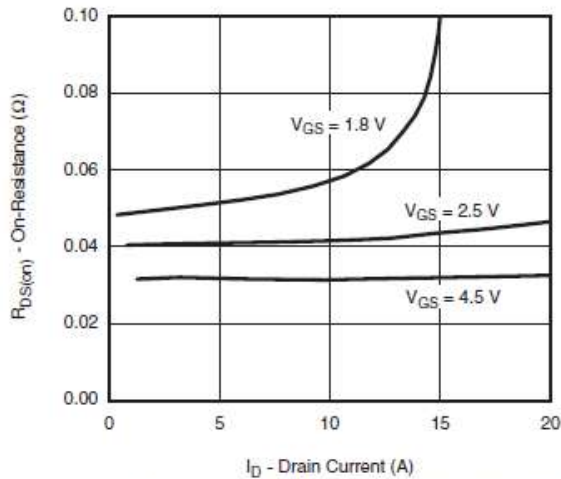
➤ Typical Characteristics



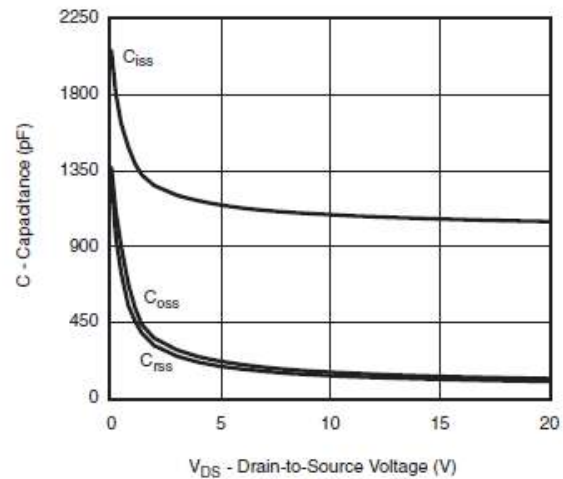
Output Characteristics



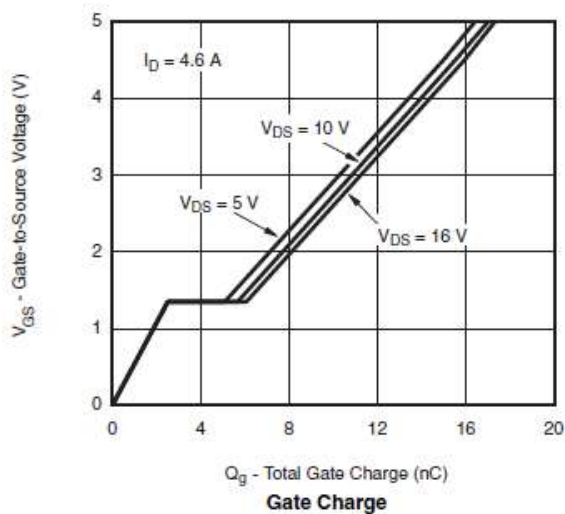
Transfer Characteristics



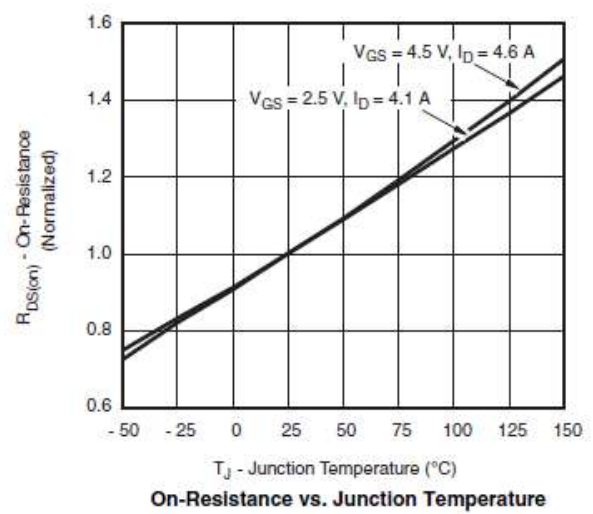
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



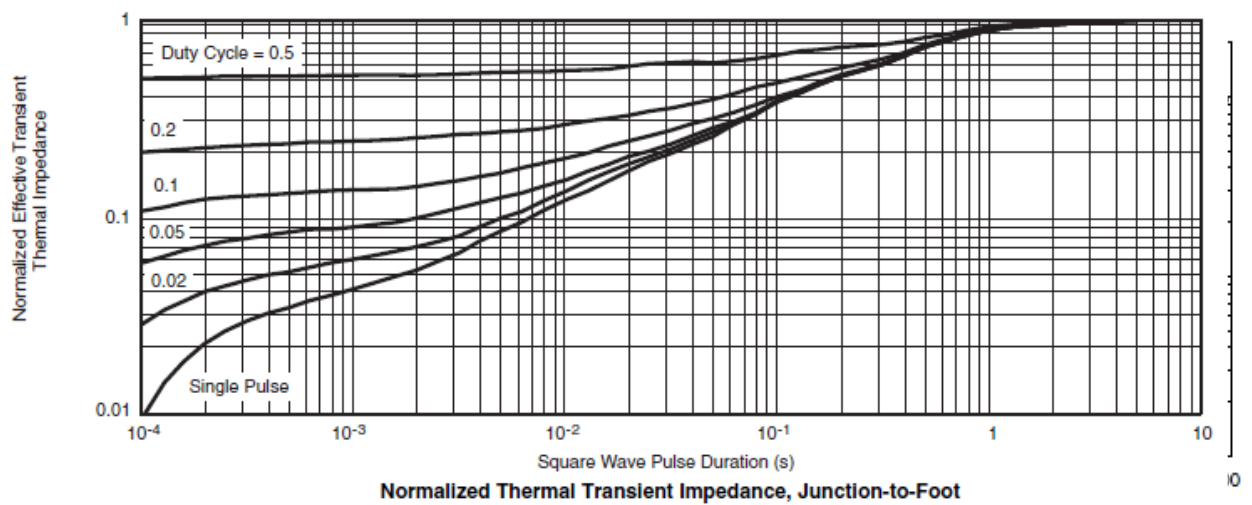
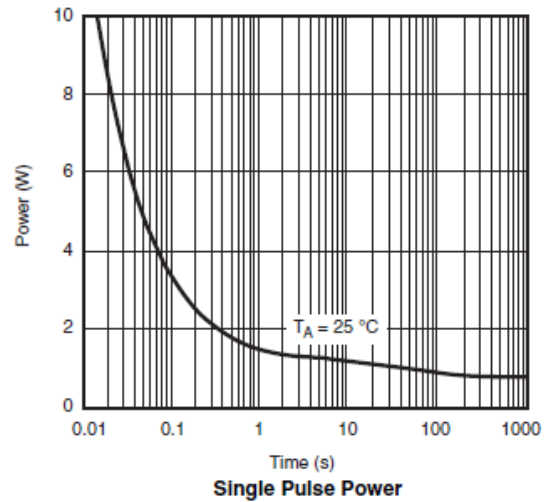
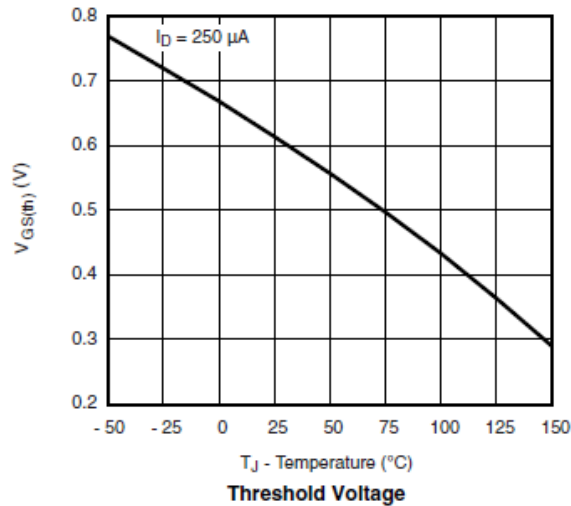
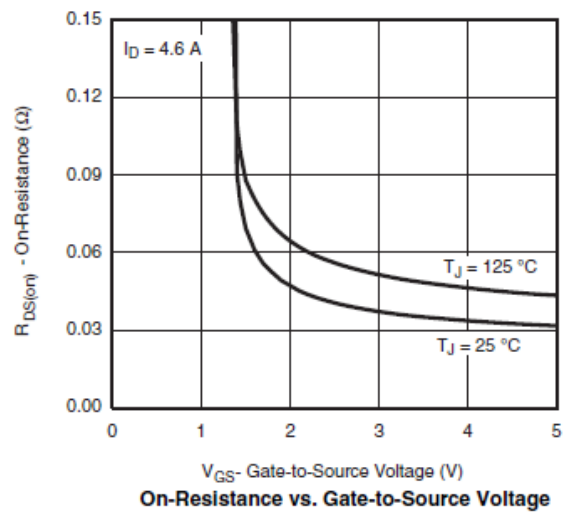
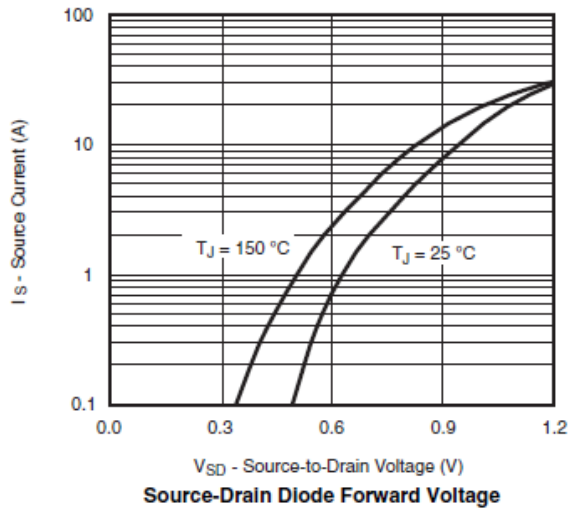
Gate Charge



On-Resistance vs. Junction Temperature

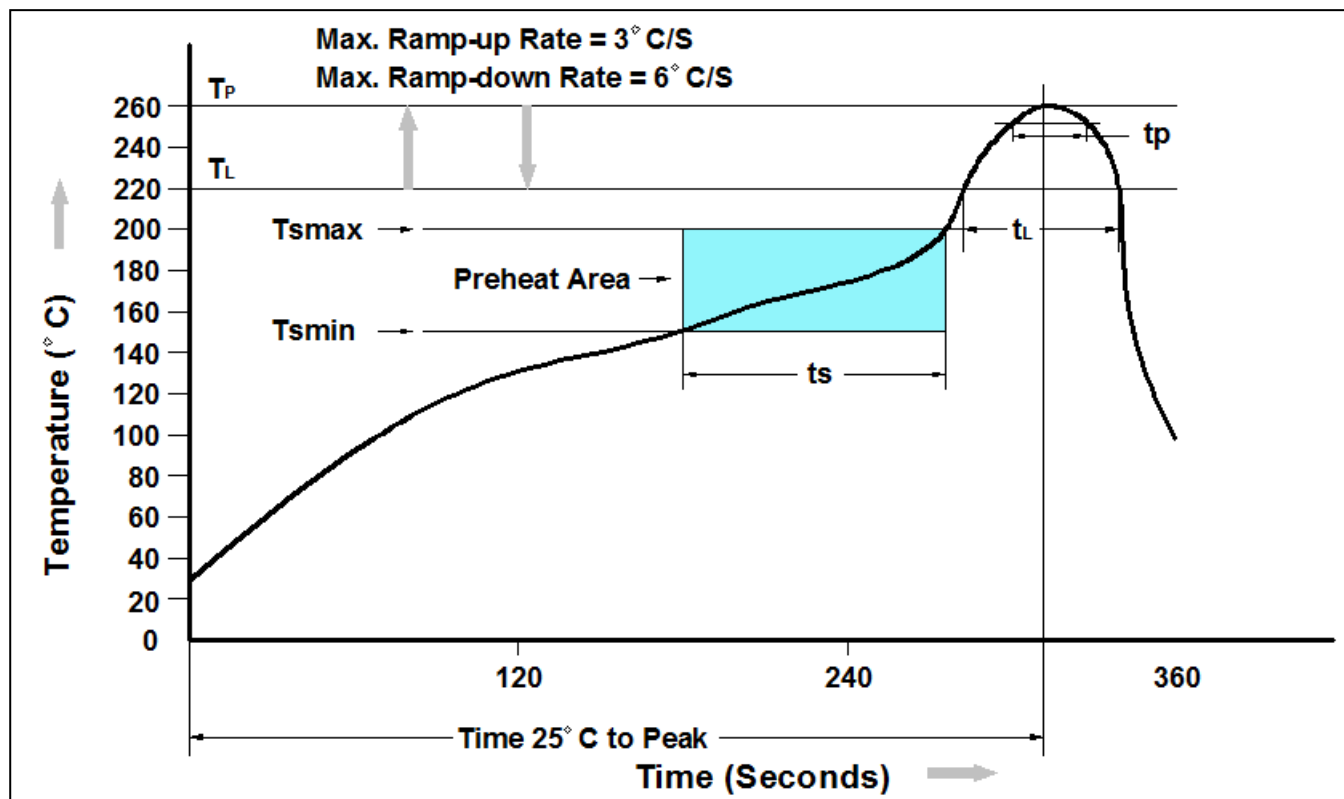
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➤ Recommend IR Reflow Soldering Thermal Profile



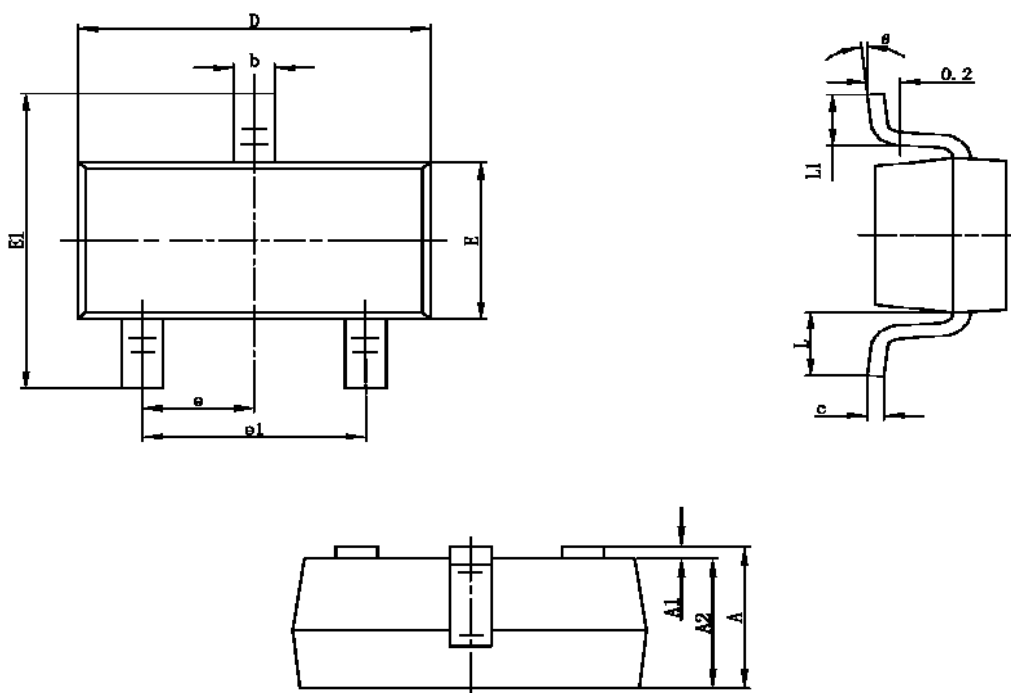
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAP2015N	SOT-23 Reel	3000 pcs

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➤ Package Information (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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